

IN THE ABSTRACT:

On page 18, in line 1, cancel "Abstract" substitute the following centered heading therefor:

--ABSTRACT OF THE DISCLOSURE--;

5 cancel lines 2-13, substitute the following abstract therefor:

-- In order to produce a vertical MOS transistor, a mask with an opening is formed on a semiconductor substrate. A layer sequence, which has a lower source/drain region, a channel region and an upper source/drain region, is grown in the opening by selective epitaxy. In this case, facets are formed on the edge of the layer sequence, so that the layer thicknesses at the edge are less than in the middle. A gate dielectric and a gate electrode are formed on the edge of the layer sequence.--

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REMARKS:

The present Amendment revises the specification, drawings and claims to conform to United States patent practice, before examination of the present PCT application in the United States National Examination Phase. All of the changes are editorial and no new matter is added thereby. The cancellation of claims 1-5, in favor of new claims 6-10, has been made solely for convenience, since the amount of bracketing and underlining necessary to editorially amend claims 1-5 in order to conform to United States patent practice would have been excessive and burdensome. The cancellation of claims 1-5 is therefore not intended to be a surrender of any of the subject matter of those claims.

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